

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-20V	400mΩ@-4.5V	-0.66A
	570mΩ@-2.5V	
	810mΩ@-1.8V	

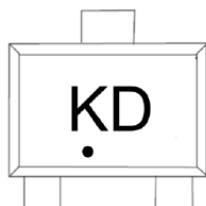
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(on)}$
- Low Gate Charge

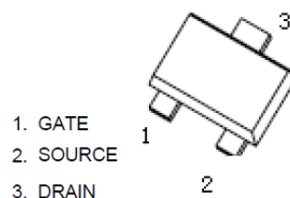
Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

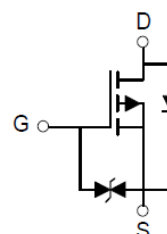
MARKING:



SOT-723



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current ^{1,5}	$T_A = 25^\circ\text{C}$	I_D	-0.66	A
	$T_A = 100^\circ\text{C}$		-0.42	
Pulsed Drain Current ²		I_{DM}	-2.64	A
Power Dissipation ^{4,5}		P_D	0.2	W
Thermal Resistance from Junction to Ambient ⁵		$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~ +150	$^\circ\text{C}$

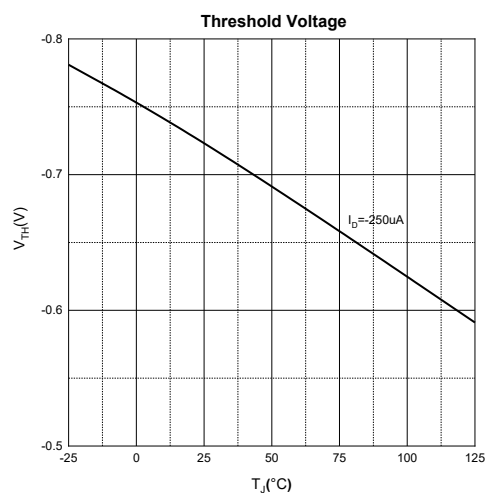
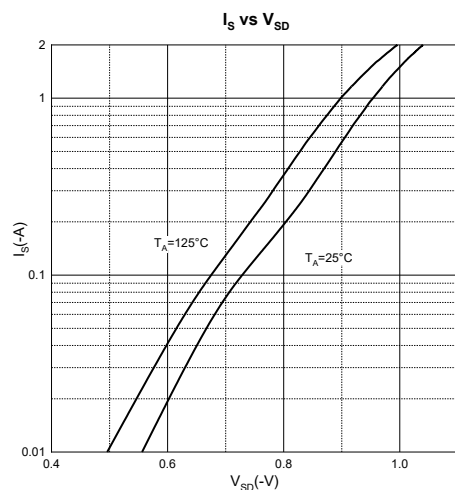
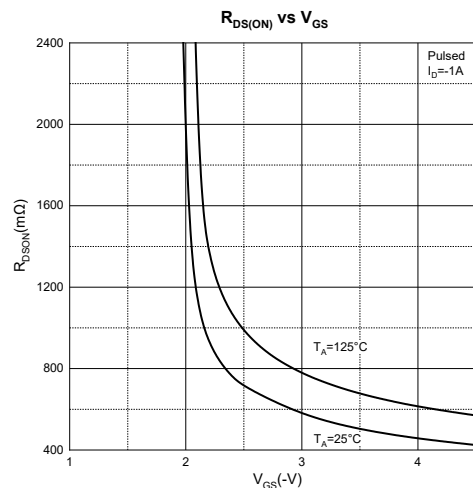
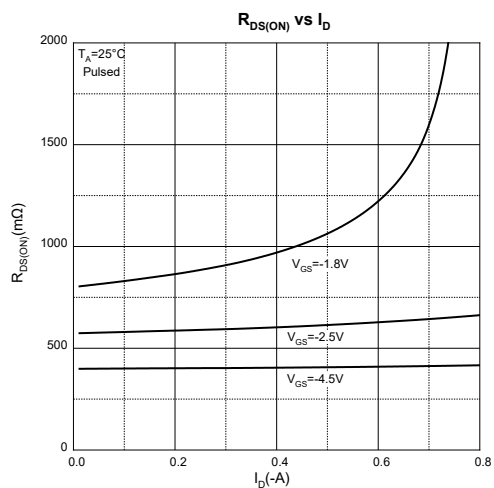
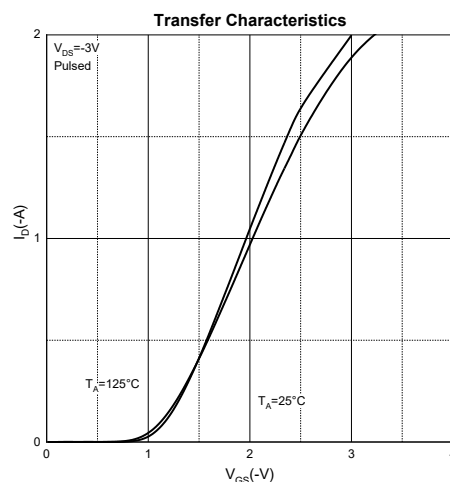
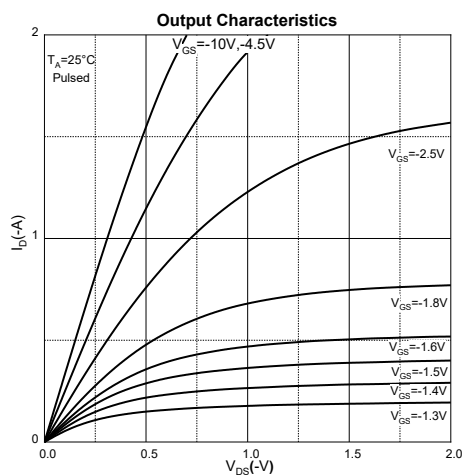
MOSFET ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

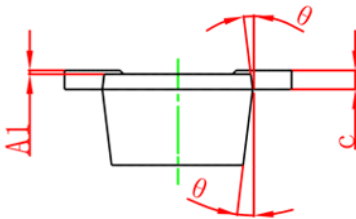
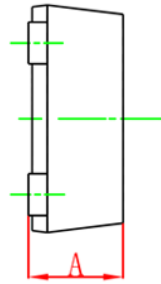
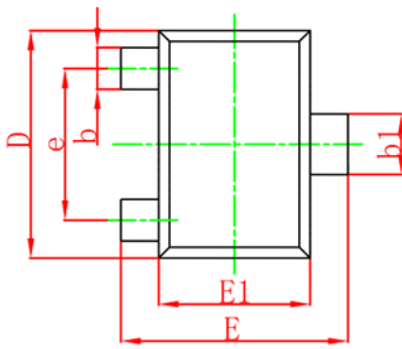
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16V, V_{GS} = 0V$			-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 10	μA
On Characteristics ³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.7	-1.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -0.5A$		400	520	m Ω
		$V_{GS} = -2.5V, I_D = -0.3A$		570	780	
		$V_{GS} = -1.8V, I_D = -0.12A$		810	1100	
Dynamic Characteristics ⁴						
Input Capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		35.5		pF
Output Capacitance	C_{oss}			5.6		
Reverse Transfer Capacitance	C_{rss}			3.5		
Switching Characteristics ⁴						
Total Gate Charge	Q_g	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -1A$		0.99		nC
Gate-Source Charge	Q_{gs}			0.28		
Gate-Drain Charge	Q_{gd}			0.19		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10V, V_{GS} = -4.5V,$ $R_L = 50\Omega, R_G = 3\Omega$		8		ns
Turn-On Rise Time	t_r			5.5		
Turn-Off Delay Time	$t_{d(off)}$			30		
Turn-Off Fall Time	t_f			17		
Source-Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = -0.5A$			-1.2	V

Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.
- 5.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



SOT-723 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.340	0.500	0.013	0.020
A1	0.000	0.050	0.000	0.002
b	0.150	0.270	0.006	0.011
b1	0.200	0.370	0.008	0.015
c	0.060	0.160	0.002	0.006
D	1.100	1.300	0.043	0.051
E	1.100	1.300	0.043	0.051
E1	0.700	0.900	0.028	0.035
e	0.8TYP		0.031TYP	
θ	8°REF		8°REF	

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.